#### SILICON (Si) POWER MOSFET ▲ CEM3425



# **CEM3425**

## -30V ▲ 36mΩ ▲ -5.9A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type P-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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RoHS

REACH

#### **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	-30V
Gate-Source Voltage	V <sub>GS</sub>	±25V
Continuous Drain Current	I <sub>D</sub>	-5.9A
Pulsed Drain Current Note 1	I <sub>DM</sub>	-23.6A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

#### **APPLICATIONS**

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			4	Ŷ

#### **PIN DESCRIPTION**

Circuit Diagram	Outline • Top View	Pin No.	Description
D (5,6,7,8)	8 7 6 5 <u>A A A A</u>	1 2	Source Source
		3 4 5	Source Gate Drain
ز s (1,2,3)		6 7 8	Drain Drain Drain

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# **ELECTRICAL CHARACTERISTICS A** T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV <sub>DSS</sub>	-30			V
Zero Gate Voltage Drain Current	$V_{DS}$ = -30V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V <sub>GS(th)</sub>	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V, I_{D} = -5.3A$	R <sub>DS(ON)</sub>		36	45	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = -4.5V, I <sub>D</sub> = -4.2A	R <sub>DS(ON)</sub>		60	80	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	CISS		650		рF
Output Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	Coss		130		рF
Reverse Transfer Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		75		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD}$ = -15V, $V_{GS}$ = -10V, $I_D$ = -1A, $R_{G(ext)}$ = 6 $\Omega$	t <sub>D(ON)</sub>		10		ns
Turn-On Rise Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -1A, $R_{\text{G(ext)}}$ = 6 $\Omega$	t <sub>R</sub>		4		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -1A, $R_{\text{G(ext)}}$ = 6 $\Omega$	t <sub>D(OFF)</sub>		36		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -1A, $R_{\text{G(ext)}}$ = 6 $\Omega$	t <sub>F</sub>		6		ns
Total Gate Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -3.6A$	Q <sub>G</sub>		11.2		nC
Gate Source Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -3.6A$	Q <sub>GS</sub>		1.7		nC
Gate Drain Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_D$ = -3.6A	$\mathbf{Q}_{GD}$		2		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		١ <sub>s</sub>			-2	А
Drain-Source Diode Forward Voltage Note 3	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2A	$V_{\text{SD}}$			-1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, t  $\leq$  10 sec

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

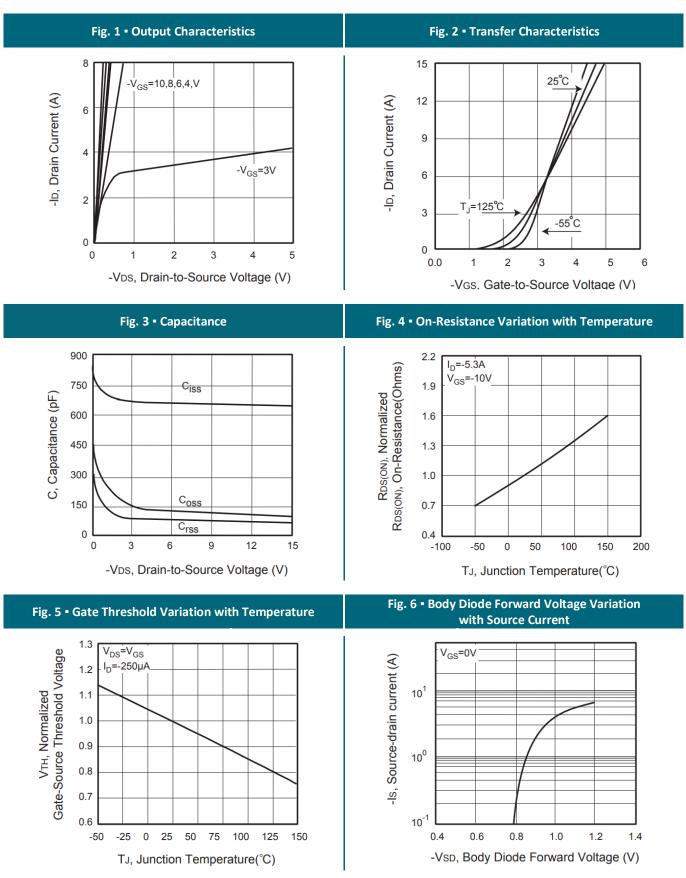
4: Guaranteed by design, not subject to production testing.



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## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



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#### **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

Fig. 7 • Gate Charge 10 V<sub>DS</sub>=-15V -VGS, Gate to Source Voltage (V) I<sub>D</sub>=-3.6A 8 6 4 2 0 0 3 6 9 12 Qg, Total Gate Charge (nC)

Fig. 9 - Breakdown Voltage Variation vs. Temperature

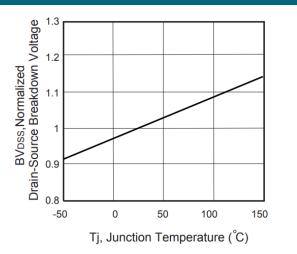
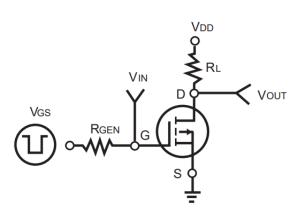


Fig. 10 - Switching Test Circuit



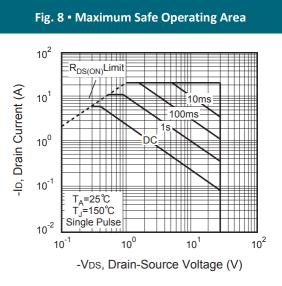
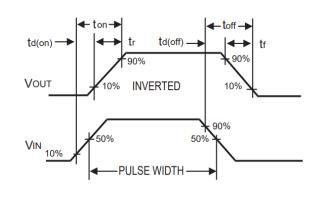


Fig. 11 • Switching Waveforms





## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

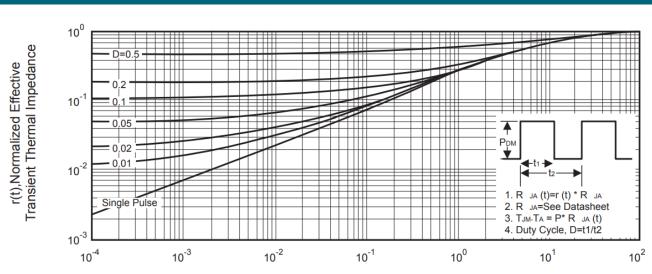
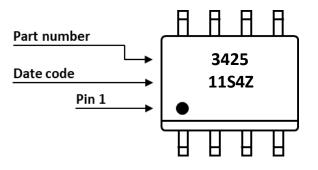


Fig. 12 • Normalized Thermal Transient Impedance Curve

Square Wave Pulse Duration (sec)

#### **PART MARKING**



#### DATE CODE

Example: 11S4Z



1	2	3	4	5	6	7	8	9	Α
01	02	03	04	05	06	07	08	09	10
В	С	D	Ε	F	G	Н	I	J	K
11	12	13	14	15	16	17	18	19	20
L	Μ	Ν	0	Ρ	Q	R	S	Т	U
21	22	23	24	25	26	27	28	29	30
V									
31									

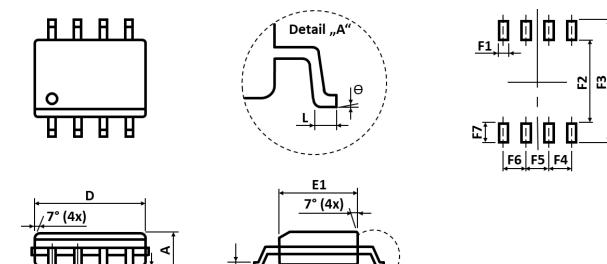
Coding list for "Month"



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## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters Millimeters (Min.) (Typ.)		
А	1.350	-	1.750	E1	3.700		4.060	
A1	0.100	-	0.250	eB	5.800		6.200	
В	0.310	-	0.510	е		1.270		
С	0.170	-	0.250	L	0.400		0.950	
D	4.690	-	5.000	θ 0°		-	8°	
<b>C</b>	Millimeters	Millimeters	Millimeters	<b>C</b>	Millimeters	Millimeters	Millimeters	

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	_	0.500	-	F5	_	1.270	-
11	-	0.300	-	IJ	-	1.270	-
F2	-	4.250	-	F6	-	1.270	-
F3	-	6.250	-	F7	-	1.000	-
F4	-	1.270	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

## **ORDERING INFORMATION**

В

A1

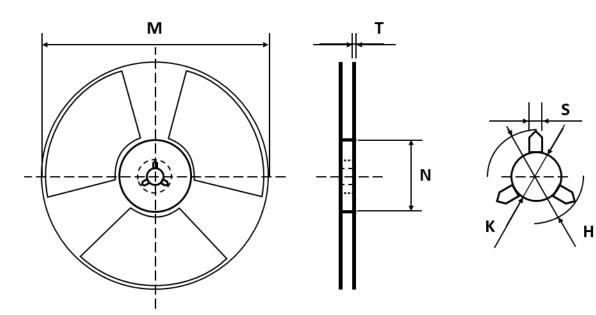
Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEM3425	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs	

• Detail "A"



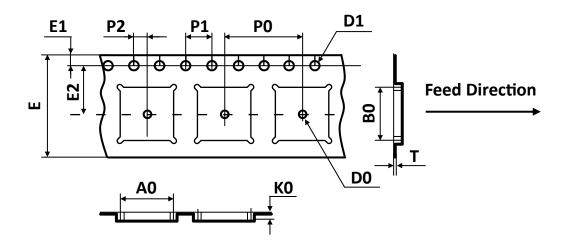


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	т	н	К	S
12mm	<i>d</i> 220	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	Ø330	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

#### **TAPE DIMENSIONS** All dimensions in mm



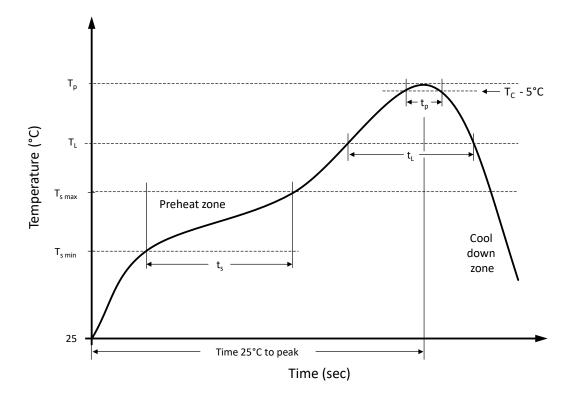
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
508	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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